



40V P-Channel Enhancement Mode MOSFET

Voltage

-40 V

Current

-16 A

Features

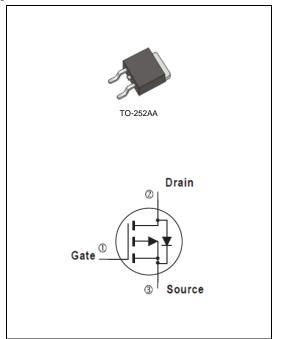
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-10A<45m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-5A<68m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _C =25°C	l _D	-16	A	
	T _C =100°C		-10		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-64		
Power Dissipation	T _C =25°C	Po	22	10/	
	T _C =100°C		9	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	-5	А	
	T _A =70°C		-4		
Power Dissipation	T _A =25°C	Po	2	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	31	mJ	
Operating Junction and Storage Temperature Range		T_J , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	5.7	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.65	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10A	-	37	45	mΩ	
		V _{GS} =-4.5V, I _D =-5A	-	57	68		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_{g}	V _{DS} =-20V, I _D =-5A, V _{GS} =-4.5V ^(Note 1,2)	-	8.3	-	nC	
Gate-Source Charge	Q_gs		-	2.6	-		
Gate-Drain Charge	Q_gd		-	2.7	-		
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V, f=1MHZ	-	929	-	pF	
Output Capacitance	Coss		-	84	-		
Reverse Transfer Capacitance	Crss	I=IIVIIIZ	-	60	-		
Turn-On Delay Time	td _(on)	V_{DS} =-20V, I_{D} =-1A, V_{GS} =-4.5V, R_{G} =6 Ω (Note 1,2)	-	26	-		
Turn-On Rise Time	t _r		-	27	-	ns	
Turn-Off Delay Time	td _(off)		-	66	-		
Turn-Off Fall Time	t _f		-	40	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,		-	-	-16	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.75	-1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =-25A, V_{DD} =-25V, V_{GS} =-10V, Starting T_J =25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

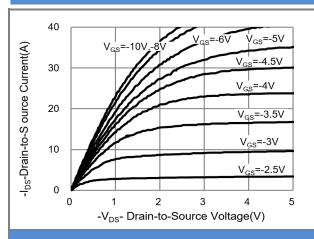


Fig.1 On-Region Characteristics

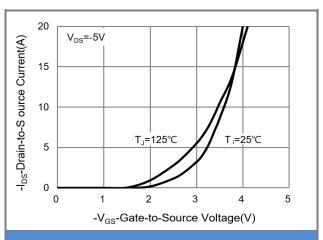


Fig.2 Transfer Characteristics

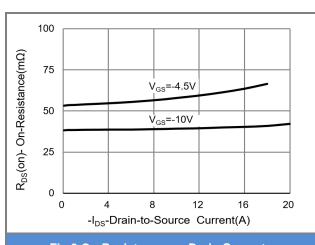


Fig.3 On-Resistance vs. Drain Current

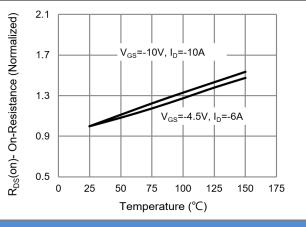


Fig.4 On-Resistance vs. Junction temperature

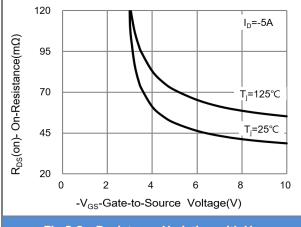
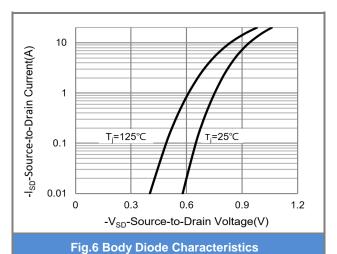


Fig.5 On-Resistance Variation with V_{GS}







TYPICAL CHARACTERISTIC CURVES

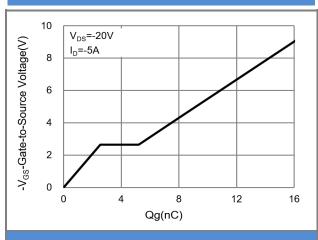


Fig.7 Gate-Charge Characteristics

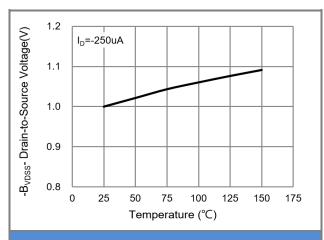


Fig.8 Breakdown Voltage Variation vs. Temperature

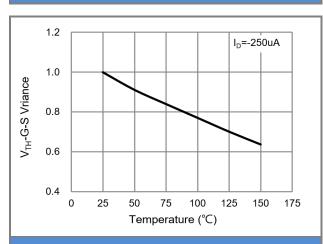


Fig.9 Threshold Voltage Variation with Temperature

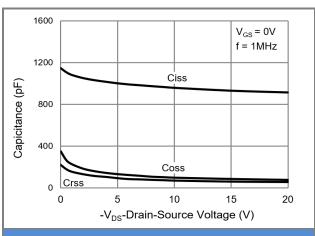


Fig.10 Capacitance vs. Drain-Source Voltage

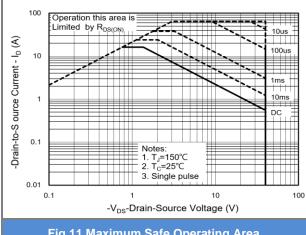


Fig.11 Maximum Safe Operating Area

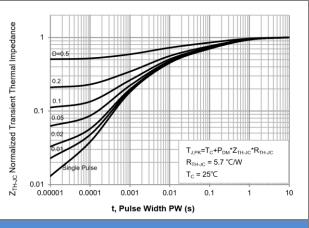


Fig.12 Normalized Thermal Transient Impedance

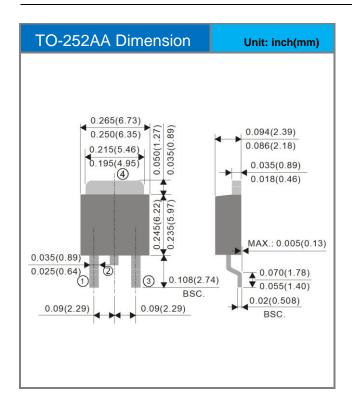


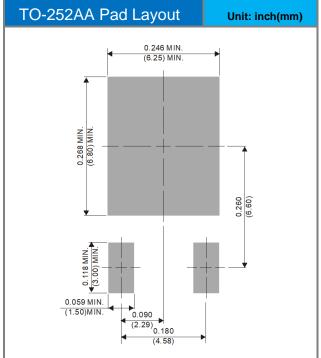


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD16P04_L2_00001	TO-252AA	3,000pcs / 13" reel	D16P04	Halogen free	

Packaging Information & Mounting Pad Layout









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